# Declaration and Power of Attorney For Patent Application

### 特許出願宣言書及び委任状

## Japanese Language Declaration

### 日本語宣言書

As a below narrd inventor, I hereby declar hat:			
My residence, post office address and citizenship are as stated next to my name.			
I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled			
SEMICONDUCTOR DEVICE AND METHOD OF			
FABRICATING THE SAME			
the specification of which is attached hereto unless the following box is checked:			
was filed on 12/23/99 as United States Application Number or PCT International Application Number  09/472,13/			
I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.			
I acknowledge the duty to disclose information which is material to patentability as defined in Title 37. Code of Federal Regulations, Section 1.56.			

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### Japan se Languag D claration (日本語宣言書)

私に、米国法典第35福119条(a)-(d) 項又は365条(b) 項に基さ下記の、 米国以外の国の少なくとも一ヵ国を指定している行許協力条約365(a)項に基づく国際出難、又は外国での行許出離もしくは楚明不証の出離についての外国任先權を二二に主導するとともに、優先權を主張している、本出離の前に出難された行弃または楚明不証の外国出離を以下に、枠内をマークすることで、示しています。

### Prior Foreign Application(s)

Prior Foreign Application(3) 外国での先行出版 10-377418	Japan (Country)
(Number)	( <b>国名</b> )
11-008494	Japan
(Number)	(Country)
(출サ)	(闰名)

私に、第35届米国法典119条(e) 項に基いて下記の米 国特許出顧規定に記載された権利をここに主張いたします。

(Application No.) (Filing Date) (出題日)

私は、下記の米国法典第35월120条に基いて下記の米国特許出頭に記載された権利、又は米国を指定している特許協力条約365条(c)に基ずく権利をここに主張します。また、本出版の各議求範囲の内容が米国法典第35월112条第1項又は特許協力条約で規定された方法で先行する米国特許出題に開示されていない限り、その先行米国出版書提出日以降で本出面書の日本国内または特許協力条約国際提出日立での期間中に入手された、運邦規則法典第37월1条56項で定義された特許資格の有無に関する重要な情報について開示義務があることを認識しています。

(Application No.) (Filing Date) (出類日)
(出類日)
(Application No.) (Filing Date) (出類日)

私は、私日身の知識に基づいて本宣言書中で利が行なう姿明が真実であり、かつ私の入手した情報と私の信じるところに基づく表明が全て真実であると信じていること。さらに放送になされた虚偽の表明及びそれと同等の行為は米国法典第18編第1001条に基づき、罰金または拘禁、もしくはその両方により処罰されること。そしてそのような政意による虚偽の声明を行なえば、出類した。又は近に許可された特許の有効性が失われることを認識し、よってここに上記のごとく宣誓を致します。

I hereby claim foreign priority under Title 35, United States Code, Section 119 (a)-(d) or 365(b) of any foreign application(s) for patent or inventor's cartificate, or 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed.

Priority Not Claimed 優先機半張なし

December 29、1998

(Day/Month/Year Filed)

(出版年月日)

January 14, 1999

(Day/Month/Year Filed)

(出版年月日)

I hereby claim the benefit under Title 35. United States Code. Section 119(e) of any United States provisional application(s) listed below.

(Application No.) (Filing Date) (出題日)

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code Section 112. I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of application.

(Status: Patented, Pending, Abandoned) (現況: 特許許可濟、係属中、放張済)

(Status: Patented, Pending, Abandoned) (現況: 特許許可済、係属中、放棄済)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Approved for use through 9/30/98. OMB 0651-0032
Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

### Japanese Language Declarati n (日本語宣言書)

委任状: 私は下記の発明者として、本出版に関する一切の 手続きを米特許商標局に対して遂行する弁理上または代理人 として、下記の者を指名いたします。(弁護士、または代理 人の氏名及び登録番号を明記のこと)

Edward D. Manzo, Reg. 28,139

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith (list name and registration number)

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#### Attorney Docket <u>0553-0152.02</u>

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Shunpei YAMAZAKI et al

Serial No: Not Assigned

Filed: Herewith

For: SEMICONDUCTOR DEVICE AND METHOD

OF FABRICATING THE SAME

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

"Express Mail" Mailing Label No. EV 321715743

Date of Deposit October 14, 2003

I hereby certify that this correspondence is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR1.10 on the date indicated above and is addressed to: Commissioner for Patents, 9.0. Box 1450, Alexandria, VA 22313-1450

Nome: ARMANDO CHING (typed or printed)

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#### APPOINTMENT OF ASSOCIATE ATTORNEYS

Sir:

Please recognize the following as my associate attorneys in the above captioned application:

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